



GP1M016A025FG Information



For Reference Only

Part Number GP1M016A025FG

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 250V 16A TO220F

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









GP1M016A025FG Specifications

Manufacturer Part Number GPIM016A025FG Manufacturer Global Power Technologies Group Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 16A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30.4W (Tc) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series - FET Type N-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Q40 mOhm @ 8A, 10V Operating Temperature MosfET (Metal Oxide) Through Hole Supplier Device Package Package / Case TO-220F Package / Case	Manufacturer Part Number	GP1M016A025FG
Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 16A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30.4W (Tc) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Manufacturer	Global Power Technologies Group
Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 16A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30.4W (Tc) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 250V Current - Continuous Drain (Id) @ 25°C 16A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 19nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30.4W (Tc) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds944pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30.4W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds944pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30.4W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	Series	-
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds944pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30.4W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 16A (Tc) 16V 16V 16V 250μA 19nC @ 10V 944pF @ 25V 944pF	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs19nC @ 10VInput Capacitance (Ciss) (Max) @ Vds944pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30.4W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case SV @ 250μA 19nC @ 10V 19nC @ 10V 944pF @ 25V +30V FET Feature - 240 W (Tc) Through Hole Through Hole TO-220F TO-220F TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	16A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 944pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)30.4W (Tc)Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	19nC @ 10V
FET Feature - Graduate	Input Capacitance (Ciss) (Max) @ Vds	944pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 240 mOhm @ 8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs240 mOhm @ 8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	30.4W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	240 mOhm @ 8A, 10V
Supplier Device Package TO-220F Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220F
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

GP1M016A025FG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP1M016A025FG Payment Methods





















GP1M016A025FG Shipping Methods













If you have any question about GP1M016A025FG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com